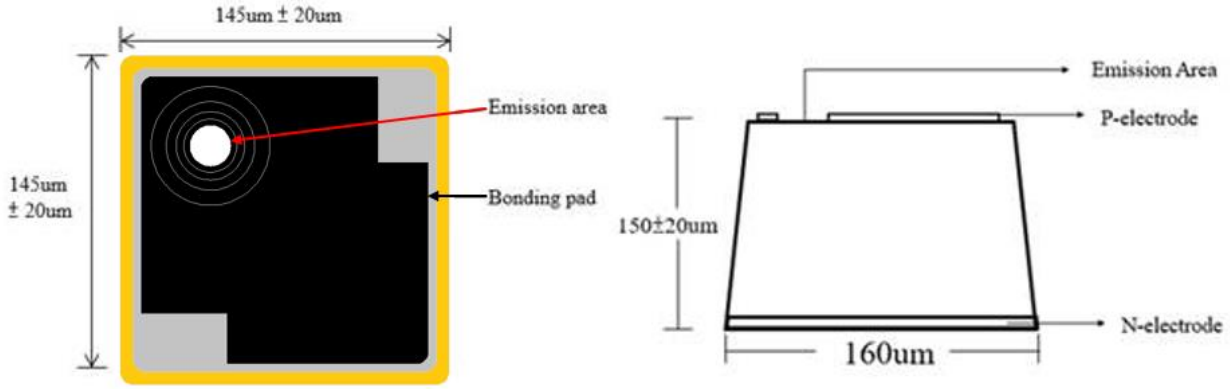
Draft

Infrared

Features & Applications :

- 940 nm Wavelength
- Low Dependence of Electrical and Optical Characteristics over Temperature
- Optical Sensing

Outline Dimensions : (Unit: um)



Physical Structure :

Chip dimension	Chip size	160 um x 160um
	Thickness	150 ± 20 um
Electrode	N(cathode)	Gold
	P (anode)	Gold

Electro-Optical Characteristics :

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Output Power	Po	IF = 10 mA	6.0	7.05	8.0	mW
Forward Voltage	VF	IF = 10 mA	1.8	2.1	2.2	V
Threshold Current	Ith	-	0.5	1.0	2.0	mA
Wavelength	λ p	IF = 10 mA	930	940	950	nm
Beam Divergence (1/e2)	θ	IF = 10 mA	-	17	-	degree

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

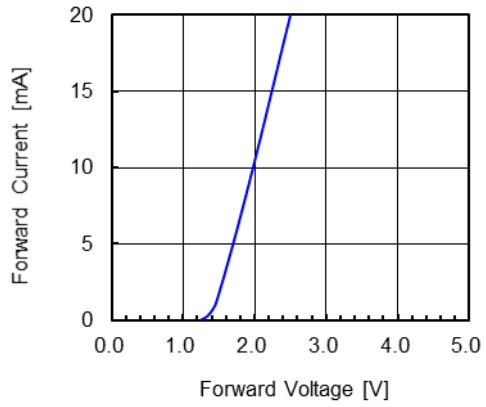


Fig 2. Relative Radiant Power vs Wavelength

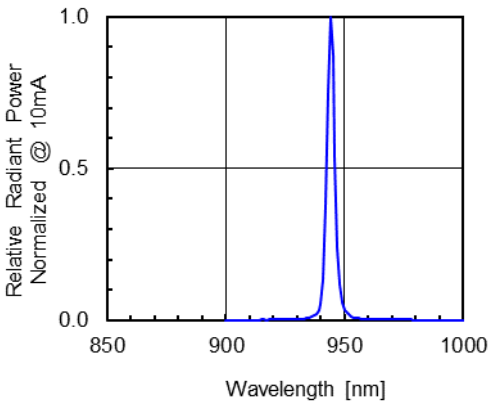


Fig 3. Relative Radiant Power vs. Forward DC Current

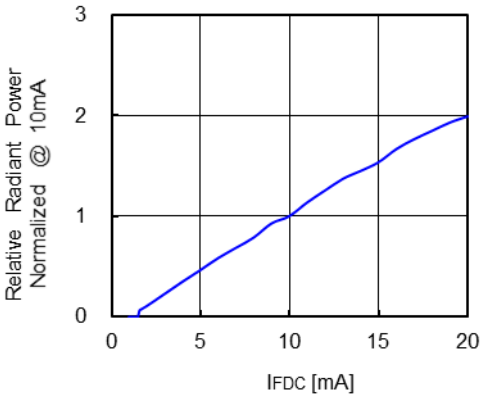


Fig 4. Relative Radiant Power vs. emission angle

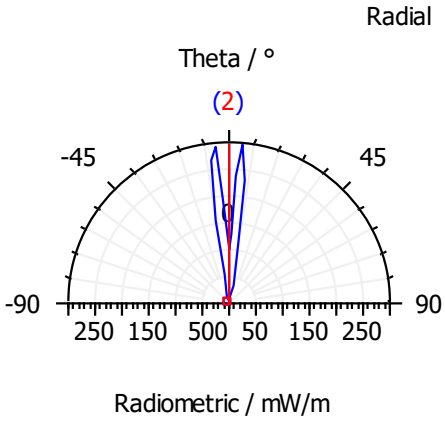


Fig 5. Forward DC Voltage vs. Temperature

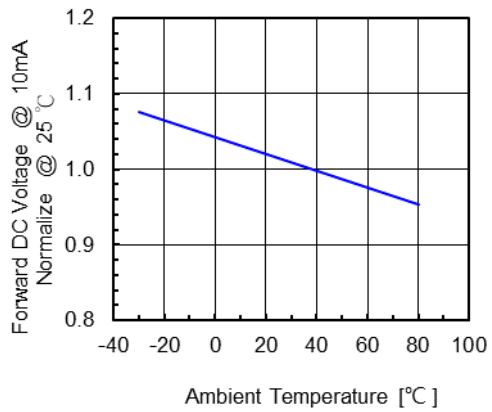


Fig 6. Relative Radiant Power vs. Temperature